

49. (new) A method of forming an insulating material comprising:
- providing a substrate within a reaction chamber;
 - providing reactants comprising silicon, fluorine and ozone within the reaction chamber; and
 - depositing an insulating material comprising fluorine, silicon and oxygen onto the substrate from the reactants, the depositing occurring at a rate of from about 1000 to about 10000 Å/min.
50. (new) The method of claim 49 wherein the depositing occurs with a plasma present in the reaction chamber.
51. (new) A method of forming a silicon oxide having Si-F bonds, comprising:
- providing a substrate within a reaction chamber;
 - providing reactants comprising ozone and a precursor having Si-F bonds; and
 - depositing a silicon oxide having Si-F bonds onto the substrate from the reactants, the depositing occurring at a rate of from about 1000 to about 10000 Å/min.
52. (new) The method of claim 51 wherein the depositing occurs with a plasma present in the reaction chamber.

Concluded
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